Lattice Semiconductor Corporation - LFE5UM-45F-6MG285C Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

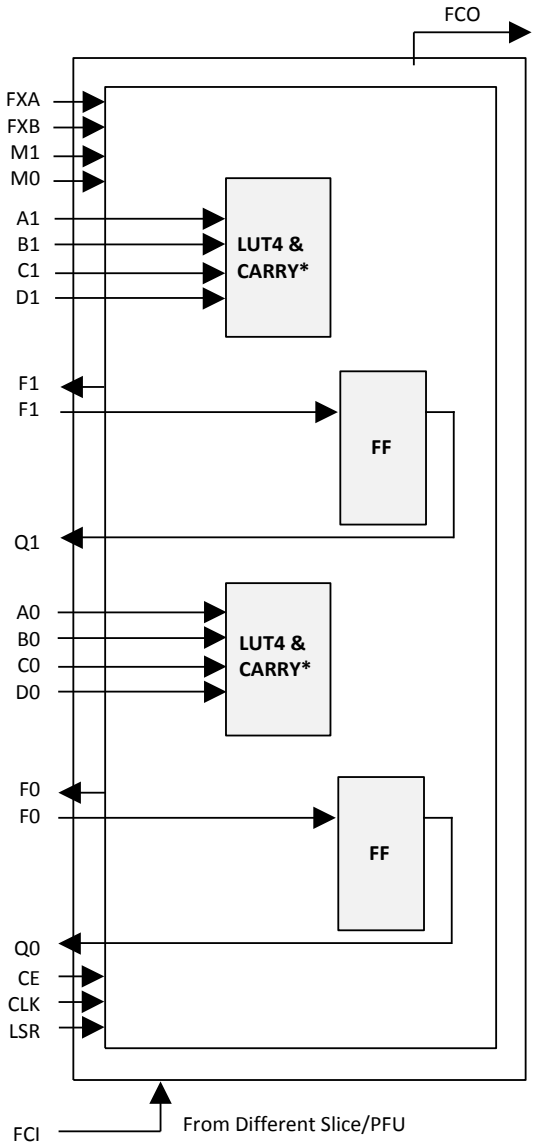
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	11000
Number of Logic Elements/Cells	44000
Total RAM Bits	1990656
Number of I/O	118
Number of Gates	-
Voltage - Supply	1.045V ~ 1.155V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	285-LFBGA, CSPBGA
Supplier Device Package	285-CSFBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe5um-45f-6mg285c

Figures



Notes: For Slices 0 and 1, memory control signals are generated from Slice 2 as follows:
WCK is CLK
WRE is from LSR
DI[3:2] for Slice 1 and DI[1:0] for Slice 0 data from Slice 2
WAD [A:D] is a 4-bit address from slice 2 LUT input

Figure 2.3. Slice Diagram

2.11. PIO

The PIO contains three blocks: an input register block, output register block, and tristate register block. These blocks contain registers for operating in a variety of modes along with the necessary clock and selection logic.

2.11.1. Input Register Block

The input register blocks for the PIOs on all edges contain delay elements and registers that can be used to condition high-speed interface signals before they are passed to the device core. In addition, the input register blocks for the PIOs on the left and right edges include built-in FIFO logic to interface to DDR and LPDDR memory.

The Input register block on the right and left sides includes gearing logic and registers to implement IDDRX1 and IDDRX2 functions. With two PICs sharing the DDR register path, it can also implement IDDRX71 function used for 7:1 LVDS interfaces. It uses three sets of registers to shift, update, and transfer to implement gearing and the clock domain transfer. The first stage registers samples the high-speed input data by the high-speed edge clock on its rising and falling edges. The second stage registers perform data alignment based on the control signals. The third stage pipeline registers pass the data to the device core synchronized to the low-speed system clock. The top side of the device supports IDDRX1 gearing function. For more information on gearing function, refer to ECP5 and ECP5-5G High-Speed I/O Interface (TN1265).

Figure 2.17 shows the input register block for the PIOs on the top edge.

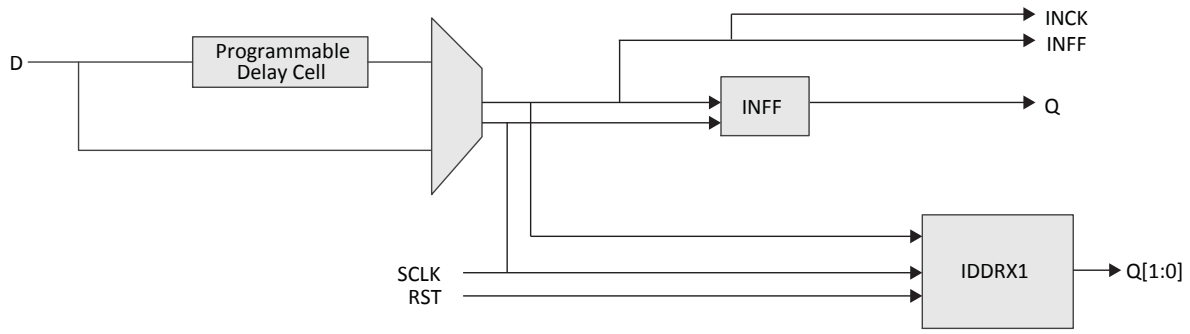
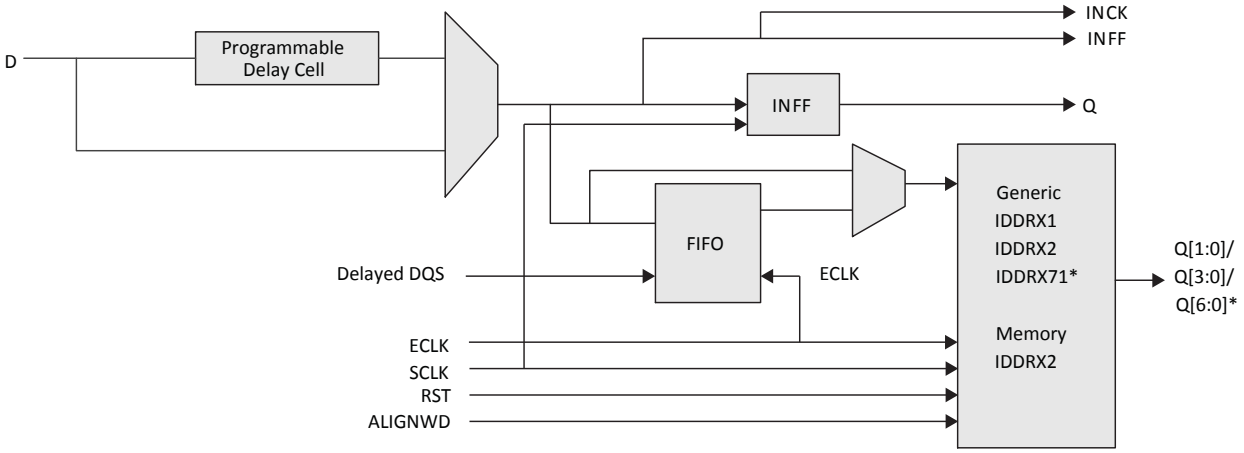


Figure 2.17. Input Register Block for PIO on Top Side of the Device

Figure 2.18 shows the input register block for the PIOs located on the left and right edges.



*For 7:1 LVDS interface only. It is required to use PIO pair pins (PIOA/B or PIOC/D).

Figure 2.18. Input Register Block for PIO on Left and Right Side of the Device

2.11.1.1. Input FIFO

The ECP5/ECP5-5G PIO has dedicated input FIFO per single-ended pin for input data register for DDR Memory interfaces. The FIFO resides before the gearing logic. It transfers data from DQS domain to continuous ECLK domain. On the Write side of the FIFO, it is clocked by DQS clock which is the delayed version of the DQS Strobe signal from DDR memory. On the Read side of FIFO, it is clocked by ECLK. ECLK may be any high speed clock with identical frequency as DQS (the frequency of the memory chip). Each DQS group has one FIFO control block. It distributes FIFO read/write pointer to every PIC in same DQS group. DQS Grouping and DQS Control Block is described in DDR Memory Support section on page 35.

Table 2.8. Input Block Port Description

Name	Type	Description
D	Input	High Speed Data Input
Q[1:0]/Q[3:0]/Q[6:0]	Output	Low Speed Data to the device core
RST	Input	Reset to the Output Block
SCLK	Input	Slow Speed System Clock
ECLK	Input	High Speed Edge Clock
DQS	Input	Clock from DQS control Block used to clock DDR memory data
ALIGNWD	Input	Data Alignment signal from device core.

2.11.2. Output Register Block

The output register block registers signal from the core of the device before they are passed to the sysIO buffers.

ECP5/ECP5-5G output data path has output programmable flip flops and output gearing logic. On the left and right sides, the output register block can support 1x, 2x and 7:1 gearing enabling high speed DDR interfaces and DDR memory interfaces. On the top side, the banks support 1x gearing. ECP5/ECP5-5G output data path diagram is shown in Figure 2.19. The programmable delay cells are also available in the output data path.

For detailed description of the output register block modes and usage, refer to ECP5 and ECP5-5G High-Speed I/O Interface (TN1265).

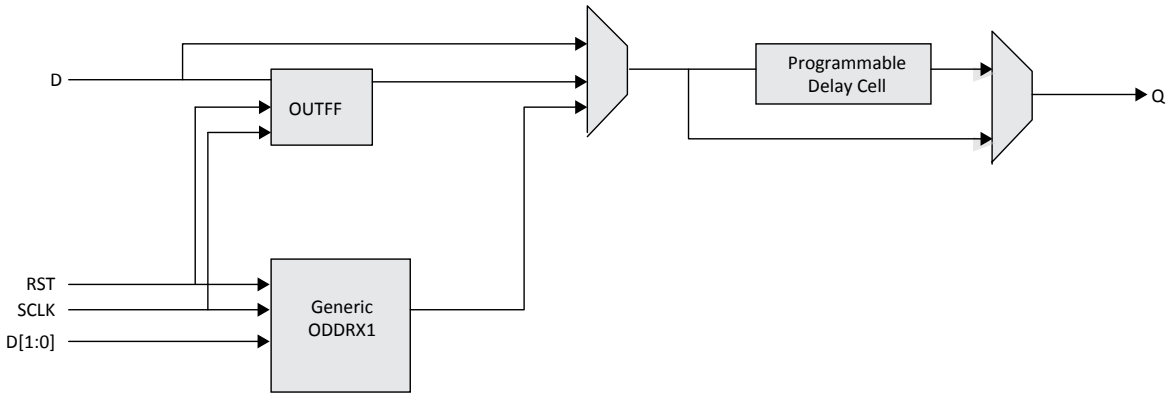


Figure 2.19. Output Register Block on Top Side

2.14. sysI/O Buffer

Each I/O is associated with a flexible buffer referred to as a sysI/O buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysI/O buffers allow users to implement the wide variety of standards that are found in today's systems including LVDS, HSUL, BLVDS, SSTL Class I and II, LVCMOS, LVTTL, LVPECL, and MIPI.

2.14.1. sysI/O Buffer Banks

ECP5/ECP5-5G devices have seven sysI/O buffer banks, two banks per side at Top, Left and Right, plus one at the bottom left side. The bottom left side bank (Bank 8) is a shared I/O bank. The I/Os in that bank contains both dedicated and shared I/O for sysConfig function. When a shared pin is not used for configuration, it is available as a user I/O. For LFE5-85 devices, there is an additional I/O bank (Bank 4) that is not available in other device in the family.

In ECP5/ECP5-5G devices, the Left and Right sides are tailored to support high performance interfaces, such as DDR2, DDR3, LPDDR2, LPDDR3 and other high speed source synchronous standards. The banks on the Left and Right sides of the devices feature LVDS input and output buffers, data-width gearing, and DQSBUF block to support DDR2/3 and LPDDR2/3 interfaces. The I/Os on the top and bottom banks do not have LVDS input and output buffer, and gearing logic, but can use LVCMOS to emulate most of differential output signaling.

Each sysIO bank has its own I/O supply voltage (V_{CCIO}). In addition, the banks on the Left and Right sides of the device, have voltage reference input (shared I/O pin), VREF1 per bank, which allow it to be completely independent of each other. The V_{REF} voltage is used to set the threshold for the referenced input buffers, such as SSTL. Figure 2.25 shows the seven banks and their associated supplies.

In ECP5/ECP5-5G devices, single-ended output buffers and ratioed input buffers (LVTTL, and LVCMOS) are powered using V_{CCIO}. LVTTL, LVCMOS33, LVCMOS25 and LVCMOS12 can also be set as fixed threshold inputs independent of V_{CCIO}.

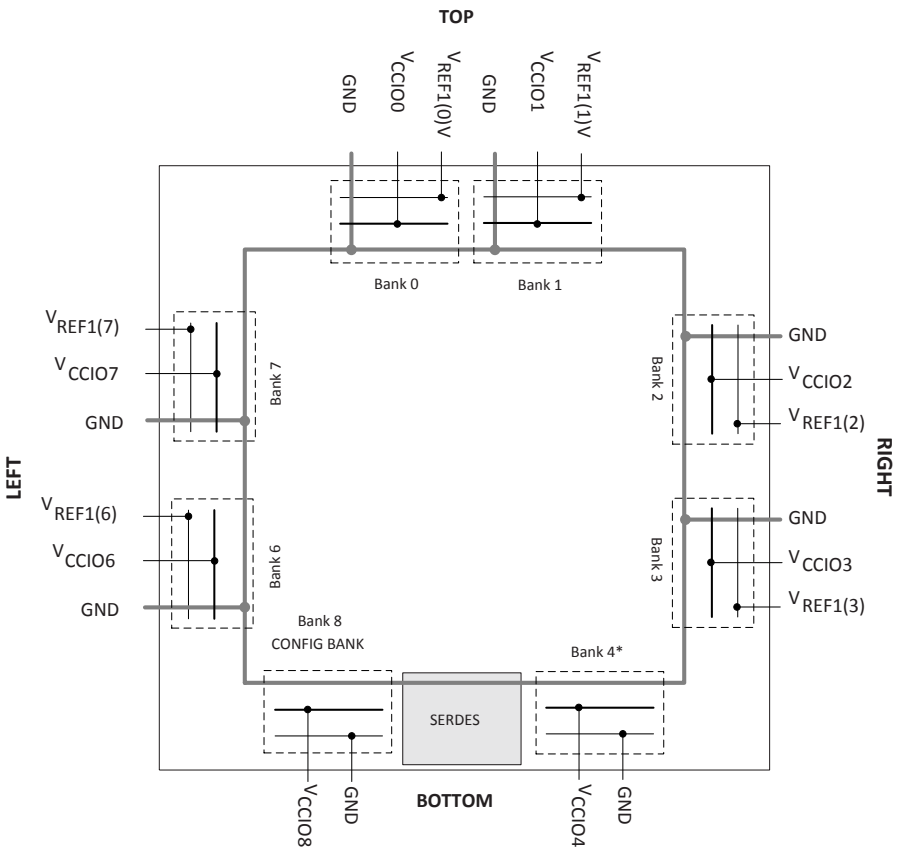


Figure 2.25. ECP5/ECP5-5G Device Family Banks

ECP5/ECP5-5G devices contain two types of sysI/O buffer pairs:

- Top (Bank 0 and Bank 1) and Bottom (Bank 8 and Bank 4) sysIO Buffer Pairs (Single-Ended Only)

  The sysI/O buffers in the Banks at top and bottom of the device consist of ratioed single-ended output drivers and single-ended input buffers. The I/Os in these banks are not usually used as a pair, except when used as emulated differential output pair. They are used as individual I/Os and be configured as different I/O modes, as long as they are compatible with the V_{CCIO} voltage in the bank. When used as emulated differential outputs, the pair can be used together.

  The top and bottom side IOs also support hot socketing. They support IO standards from 3.3 V to 1.2 V. They are ideal for general purpose I/Os, or as ADDR/CMD bus for DDR2/DDR3 applications, or for used as emulated differential signaling.

  Bank 4 I/O only exists in the LFE5-85 device.

  Bank 8 is a bottom bank that shares with sysConfig I/Os. During configuration, these I/Os are used for programming the device. Once the configuration is completed, these I/Os can be released and user can use these I/Os for functional signals in his design.

  The top and bottom side pads can be identified by the Lattice Diamond tool.

- Left and Right (Banks 2, 3, 6 and 7) sysI/O Buffer Pairs (50% Differential and 100% Single-Ended Outputs)

  The sysI/O buffer pairs in the left and right banks of the device consist of two single-ended output drivers, two single-ended input buffers (both ratioed and referenced) and half of the sysI/O buffer pairs (PIOA/B pairs) also has a high-speed differential output driver. One of the referenced input buffers can also be configured as a differential input. In these banks the two pads in the pair are described as “true” and “comp”, where the true pad is associated with the positive side of the differential I/O, and the comp (complementary) pad is associated with the negative side of the differential I/O.

  In addition, programmable on-chip input termination (parallel or differential, static or dynamic) is supported on these sides, which is required for DDR3 interface. However, there is no support for hot-socketing for the I/O pins located on the left and right side of the device as the PCI clamp is always enabled on these pins.

  LVDS differential output drivers are available on 50% of the buffer pairs on the left and right banks.

2.14.2. Typical sysI/O I/O Behavior during Power-up

The internal Power-On-Reset (POR) signal is deactivated when V_{CC}, V_{CCIO8} and V_{CCAUX} have reached satisfactory levels. After the POR signal is deactivated, the FPGA core logic becomes active. It is the user’s responsibility to ensure that all other V_{CCIO} banks are active with valid input logic levels to properly control the output logic states of all the I/O banks that are critical to the application. For more information about controlling the output logic state with valid input logic levels during power-up in ECP5/ECP5-5G devices, see the list of technical documentation in Supplemental Information section on page 102.

The V_{CC} and V_{CCAUX} supply the power to the FPGA core fabric, whereas the V_{CCIO} supplies power to the I/O buffers. In order to simplify system design while providing consistent and predictable I/O behavior, it is recommended that the I/O buffers be powered-up prior to the FPGA core fabric. V_{CCIO} supplies should be powered-up before or together with the V_{CC} and V_{CCAUX} supplies.

2.14.3. Supported sysI/O Standards

The ECP5/ECP5-5G sysI/O buffer supports both single-ended and differential standards. Single-ended standards can be further subdivided into LVCMOS, LVTTL and other standards. The buffers support the LVTTL, LVCMOS 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V standards. In the LVCMOS and LVTTL modes, the buffer has individual configuration options for drive strength, slew rates, bus maintenance (weak pull-up, weak pull-down, or a bus-keeper latch) and open drain. Other single-ended standards supported include SSTL and HSUL. Differential standards supported include LVDS, differential SSTL and differential HSUL. For further information on utilizing the sysI/O buffer to support a variety of standards, refer to ECP5 and ECP5-5G sysIO Usage Guide (TN1262).

2.14.4. On-Chip Programmable Termination

The ECP5/ECP5-5G devices support a variety of programmable on-chip terminations options, including:

- Dynamically switchable Single-Ended Termination with programmable resistor values of 50 Ω, 75 Ω, or 150 Ω.
- Common mode termination of 100 Ω for differential inputs.

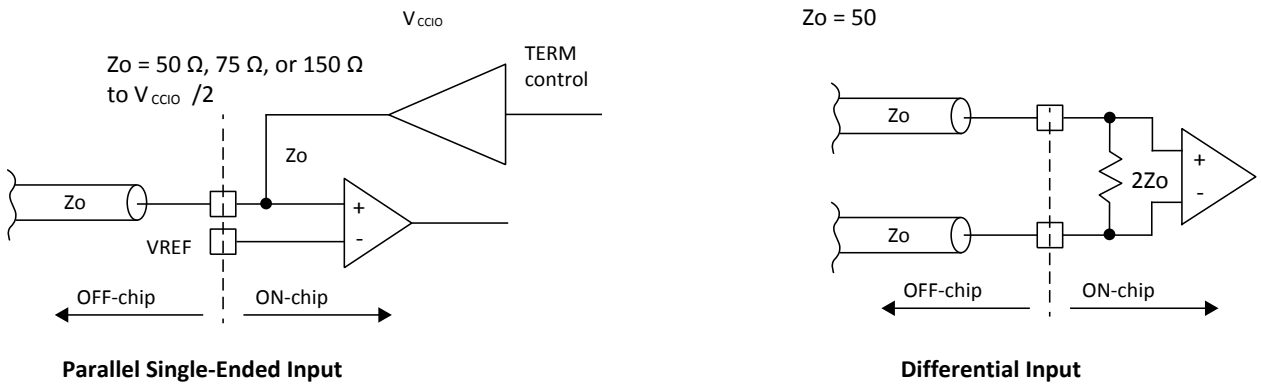


Figure 2.26. On-Chip Termination

See Table 2.12 for termination options for input modes.

Table 2.12. On-Chip Termination Options for Input Modes

IO_TYPE	Terminate to $V_{CCIO}/2$*	Differential Termination Resistor*
LVDS25	—	100
BLVDS25	—	100
MLVDS	—	100
LVPECL33	—	100
subLVDS	—	100
SLVS	—	100
HSUL12	50, 75, 150	—
HSUL12D	—	100
SSTL135_I / II	50, 75, 150	—
SSTL135D_I / II	—	100
SSTL15_I / II	50, 75, 150	—
SSTL15D_I / II	—	100
SSTL18_I / II	50, 75, 150	—
SSTL18D_I / II	—	100

***Notes**:

TERMINATE to $V_{CCIO}/2$ (Single-Ended) and DIFFRENTIAL TERMINATION RESISTOR when turned on can only have one setting per bank. Only left and right banks have this feature.

Use of TERMINATE to $V_{CCIO}/2$ and DIFFRENTIAL TERMINATION RESISTOR are mutually exclusive in an I/O bank. On-chip termination tolerance ±20%.

Refer to ECP5 and ECP5-5G sysIO Usage Guide (TN1262) for on-chip termination usage and value ranges.

2.14.5. Hot Socketing

ECP5/ECP5-5G devices have been carefully designed to ensure predictable behavior during power-up and power-down. During power-up and power-down sequences, the I/Os remain in tristate until the power supply voltage is high enough to ensure reliable operation. In addition, leakage into I/O pins is controlled within specified limits. See the Hot Socketing Specifications section on page 48.

2.15. SERDES and Physical Coding Sublayer

LFE5UM/LFE5UM5G devices feature up to 4 channels of embedded SERDES/PCS arranged in dual-channel blocks at the bottom of the devices. Each channel supports up to 3.2 Gb/s (ECP5), or up to 5 Gb/s (ECP5-5G) data rate. Figure 2.27 shows the position of the dual blocks for the LFE5-85. Table 2.13 shows the location of available SERDES Duals for all devices. The LFE5UM/LFE5UM5G SERDES/PCS supports a range of popular serial protocols, including:

- PCI Express Gen1 and Gen2 (2.5 Gb/s) on ECP5UM; Gen 1, Gen2 (2.5 Gb/s and 5 Gb/s) on ECP5-5G
- Ethernet (XAUI, GbE – 1000 Base CS/SX/LX and SGMII)
- SMPTE SDI (3G-SDI, HD-SDI, SD-SDI)
- CPRI (E.6.LV: 614.4 Mb/s, E.12.LV: 1228.8 Mb/s, E.24.LV: 2457.6 Mb/s, E.30.LV: 3072 Mb/s), also E.48.LV2:4915 Mb/s in ECP5-5G
- JESD204A/B – ADC and DAC converter interface: 312.5 Mb/s to 3.125 Gb/s (ECP5) / 5 Gb/s (ECP5-5G)

Each dual contains two dedicated SERDES for high speed, full duplex serial data transfer. Each dual also has a PCS block that interfaces to the SERDES channels and contains protocol specific digital logic to support the standards listed above. The PCS block also contains interface logic to the FPGA fabric. All PCS logic for dedicated protocol support can also be bypassed to allow raw 8-bit or 10-bit interfaces to the FPGA fabric.

Even though the SERDES/PCS blocks are arranged in duals, multiple baud rates can be supported within a dual with the use of dedicated, per channel /1, /2 and /11 rate dividers. Additionally, two duals can be arranged together to form x4 channel link.

ECP5UM devices and ECP5-5G devices are pin-to-pin compatible. But, the ECP5UM devices require 1.1 V on VCCA, VCCHRX and VCCHTX supplies. ECP5-5G devices require 1.2 V on these supplies. When designing either family device with migration in mind, these supplies need to be connected such that it is possible to adjust the voltage level on these supplies.

When a SERDES Dual in a 2-Dual device is not used, the power VCCA power supply for that Dual should be connected. It is advised to connect the VCCA of unused channel to core if the user knows he will not use the Dual at all, or it should be connected to a different regulated supply, if that Dual may be used in the future.

For an unused channel in a Dual, it is advised to connect the VCCHTX to VCCA, and user can leave VCCHRX unconnected.

For information on how to use the SERDES/PCS blocks to support specific protocols, as well on how to combine multiple protocols and baud rates within a device, refer to ECP5 and ECP5-5G SERDES/PCS Usage Guide (TN1261).

2.18. Device Configuration

All ECP5/ECP5-5G devices contain two ports that can be used for device configuration. The Test Access Port (TAP), which supports bit-wide configuration, and the sysCONFIG port, support dual-byte, byte and serial configuration. The TAP supports both the IEEE Standard 1149.1 Boundary Scan specification and the IEEE Standard 1532 In-System Configuration specification. There are 11 dedicated pins for TAP and sysConfig supports (TDI, TDO, TCK, TMS, CFG[2:0], PROGRAMN, DONE, INITN and CCLK). The remaining sysCONFIG pins are used as dual function pins. Refer to ECP5 and ECP5-5G sysCONFIG Usage Guide (TN1260) for more information about using the dual-use pins as general purpose I/Os.

There are various ways to configure an ECP5/ECP5-5G device:

- JTAG
- Standard Serial Peripheral Interface (SPI) – Interface to boot PROM Support x1, x2, x4 wide SPI memory interfaces.
- System microprocessor to drive a x8 CPU port SPCM mode
- System microprocessor to drive a serial slave SPI port (SSPI mode)
- Slave Serial model (SCM)

On power-up, the FPGA SRAM is ready to be configured using the selected sysCONFIG port. Once a configuration port is selected, it will remain active throughout that configuration cycle. The IEEE 1149.1 port can be activated any time after power-up by sending the appropriate command through the TAP port.

ECP5/ECP5-5G devices also support the Slave SPI Interface. In this mode, the FPGA behaves like a SPI Flash device (slave mode) with the SPI port of the FPGA to perform read-write operations.

2.18.1. Enhanced Configuration Options

ECP5/ECP5-5G devices have enhanced configuration features such as: decryption support, decompression support, TransFR™ I/O and dual-boot and multi-boot image support.

TransFR (Transparent Field Reconfiguration)

TransFR I/O (TFR) is a unique Lattice technology that allows users to update their logic in the field without interrupting system operation using a single ispVM command. TransFR I/O allows I/O states to be frozen during device configuration. This allows the device to be field updated with a minimum of system disruption and downtime. Refer to Minimizing System Interruption During Configuration Using TransFR Technology (TN1087) for details.

Dual-Boot and Multi-Boot Image Support

Dual-boot and multi-boot images are supported for applications requiring reliable remote updates of configuration data for the system FPGA. After the system is running with a basic configuration, a new boot image can be downloaded remotely and stored in a separate location in the configuration storage device. Any time after the update the ECP5/ECP5-5G devices can be re-booted from this new configuration file. If there is a problem, such as corrupt data during download or incorrect version number with this new boot image, the ECP5/ECP5-5G device can revert back to the original backup golden configuration and try again. This all can be done without power cycling the system. For more information, refer to ECP5 and ECP5-5G sysCONFIG Usage Guide (TN1260).

2.18.2. Single Event Upset (SEU) Support

ECP5/ECP5-5G devices support SEU mitigation with three supporting functions:

- SED – Soft Error Detect
- SEC – Soft Error Correction
- SEI – Soft Error Injection

ECP5/ECP5-5G devices have dedicated logic to perform Cycle Redundancy Code (CRC) checks. During configuration, the configuration data bitstream can be checked with the CRC logic block. In addition, the ECP5/ECP5-5G device can also be programmed to utilize a Soft Error Detect (SED) mode that checks for soft errors in configuration SRAM. The SED operation can be run in the background during user mode. If a soft error occurs, during user mode (normal operation) the device can be programmed to generate an error signal.

3.7. Hot Socketing Requirements

Table 3.6. Hot Socketing Requirements

Description	Min	Typ	Max	Unit
Input current per SERDES I/O pin when device is powered down and inputs driven.	—	—	8	mA
Input current per HDIN pin when device power supply is off, inputs driven[1, 2]	—	—	15	mA
Current per HDIN pin when device power ramps up, input driven[3]	—	—	50	mA
Current per HDOUT pin when device power supply is off, outputs pulled up[4]	—	—	30	mA

Notes:

1. Device is powered down with all supplies grounded, both HDINP and HDINN inputs driven by a CML driver with maximum allowed output V_{CCHTX}, 8b/10b data, no external AC coupling.
2. Each P and N input must have less than the specified maximum input current during hot plug. For a device with 2 DCU, the total input current would be 15 mA * 4 channels * 2 input pins per channel = 120 mA.
3. Device power supplies are ramping up (V_{CCA} and V_{CCAUX}), both HDINP and HDINN inputs are driven by a CML driver with maximum allowed output V_{CCHTX}, 8b/10b data, internal AC coupling.
4. Device is powered down with all supplies grounded. Both HDOUTP and HDOUN outputs are pulled up to V_{CCHTX} by the far end receiver termination of 50 Ω single ended.

3.8. ESD Performance

Refer to the ECP5 and ECP5-5G Product Family Qualification Summary for complete qualification data, including ESD performance.

3.9. DC Electrical Characteristics

Over Recommended Operating Conditions

Table 3.7. DC Electrical Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IL}, I_{IH}[1, 4]	Input or I/O Low Leakage	$0 \le V_{IN} \le V_{CCIO}$	—	—	10	µA
I_{IH}[1, 3]	Input or I/O High Leakage	$V_{CCIO} < V_{IN} \le V_{IH(MAX)}$	—	—	100	µA
I_{PU}	I/O Active Pull-up Current, sustaining logic HIGH state	$0.7\ V_{CCIO} \le V_{IN} \le V_{CCIO}$	–30	—	—	µA
	I/O Active Pull-up Current, pulling down from logic HIGH state	$0 \le V_{IN} \le 0.7\ V_{CCIO}$	—	—	–150	µA
I_{PD}	I/O Active Pull-down Current, sustaining logic LOW state	$0 \le V_{IN} \le V_{IL}$ (MAX)	30	—	—	µA
	I/O Active Pull-down Current, pulling up from logic LOW state	$0 \le V_{IN} \le V_{CCIO}$	—	—	150	µA
C1	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = 1.2 V, V_{IO} = 0 to $V_{IH(MAX)}$	—	5	8	pf
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = 1.2 V, V_{IO} = 0 to $V_{IH(MAX)}$	—	5	7	pf
V_{HYST}	Hysteresis for Single-Ended Inputs	V_{CCIO} = 3.3 V	—	300	—	mV
		V_{CCIO} = 2.5 V	—	250	—	mV

Notes:

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tristated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25 °C, f = 1.0 MHz.
3. Applicable to general purpose I/Os in top and bottom banks.
4. When used as V_{REF}, maximum leakage= 25 µA.

Table 3.10. ECP5-5G

Symbol	Description	Typ	Max	Unit
Standby (Power Down)				
I_{CCA-SB}	V_{CCA} Power Supply Current (Per Channel)	4	9.5	mA
$I_{CCHRX-SB}$[4]	V_{CCHRX}, Input Buffer Current (Per Channel)	—	0.1	mA
$I_{CCHTX-SB}$	V_{CCHTX}, Output Buffer Current (Per Channel)	—	0.9	mA
Operating (Data Rate = 5 Gb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	58	67	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 3.2 Gb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	48	57	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 2.5 Gb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	44	53	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 1.25 Gb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	36	46	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 270 Mb/s)				
I_{CCA-OP}	V_{CCA} Power Supply Current (Per Channel)	30	40	mA
$I_{CCHRX-OP}$[5]	V_{CCHRX}, Input Buffer Current (Per Channel)	0.4	0.5	mA
$I_{CCHTX-OP}$	V_{CCHTX}, Output Buffer Current (Per Channel)	8	10	mA

Notes:

1. Rx Equalization enabled, Tx De-emphasis (pre-cursor and post-cursor) disabled
2. Per Channel current is calculated with both channels on in a Dual, and divide current by two. If only one channel is on, current will be higher.
3. To calculate with Tx De-emphasis enabled, use the Diamond Power Calculator tool.
4. For $I_{CCHRX-SB}$, during Standby, input termination on Rx are disabled.
5. For $I_{CCHRX-OP}$, during operational, the max specified when external AC coupling is used. If externally DC coupled, the power is based on current pulled down by external driver when the input is driven to LOW.

3.13. sysI/O Single-Ended DC Electrical Characteristics

Table 3.12. Single-Ended DC Characteristics

Input/Output Standard	V_{IL}		V_{IH}		V_{OL} Max (V)	V_{OH} Min (V)	I_{OL}[1] (mA)	I_{OH}[1] (mA)
	Min (V)	Max (V)	Min (V)	Max (V)				
LVCMOS33	–0.3	0.8	2.0	3.465	0.4	V_{CCIO} – 0.4	16, 12, 8, 4	–16, –12, –8, –4
LVCMOS25	–0.3	0.7	1.7	3.465	0.4	V_{CCIO} – 0.4	12, 8, 4	–12, –8, –4
LVCMOS18	–0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.465	0.4	V_{CCIO} – 0.4	12, 8, 4	–12, –8, –4
LVCMOS15	–0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.465	0.4	V_{CCIO} – 0.4	8, 4	–8, –4
LVCMOS12	–0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.465	0.4	V_{CCIO} – 0.4	8, 4	–8, –4
LVTTL33	–0.3	0.8	2.0	3.465	0.4	V_{CCIO} – 0.4	16, 12, 8, 4	–16, –12, –8, –4
SSTL18_I (DDR2 Memory)	–0.3	V_{REF} – 0.125	V_{REF} + 0.125	3.465	0.4	V_{CCIO} – 0.4	6.7	–6.7
SSTL18_II	–0.3	V_{REF} –	V_{REF} + 0.125	3.465	0.28	V_{CCIO} – 0.28	13.4	–13.4
SSTL15 _I (DDR3 Memory)	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.465	0.31	V_{CCIO} – 0.31	7.5	–7.5
SSTL15_II (DDR3 Memory)	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.465	0.31	V_{CCIO} – 0.31	8.8	–8.8
SSTL135_I (DDR3L Memory)	–0.3	V_{REF} – 0.09	V_{REF} + 0.09	3.465	0.27	V_{CCIO} – 0.27	7	–7
SSTL135_II (DDR3L Memory)	–0.3	V_{REF} – 0.09	V_{REF} + 0.09	3.465	0.27	V_{CCIO} – 0.27	8	–8
MIPI D-PHY (LP)[3]	–0.3	0.55	0.88	3.465	—	—	—	—
HSUL12 (LPDDR2/3 Memory)	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.465	0.3	V_{CCIO} – 0.3	4	–4

Notes:

1. For electromigration, the average DC current drawn by the I/O pads within a bank of I/Os shall not exceed 10 mA per I/O (All I/Os used in the same V_{CCIO}).
2. Not all IO types are supported in all banks. Refer to ECP5 and ECP5-5G sysIO Usage Guide (TN1262) for details.
3. MIPI D-PHY LP input can be implemented by powering VCCIO to 1.5V, and select MIPI LP primitive to meet MIPI Alliance spec on V_{IH} and V_{IL}. It can also be implemented as LVCMOS12 with VCCIO at 1.2V, which would meet V_{IH}/V_{IL} spec on LVCOM12.

3.14.6. **LVPECL33**

The ECP5/ECP5-5G devices support the differential LVPECL standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The LVPECL input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3.3 is one possible solution for point-to-point signals.

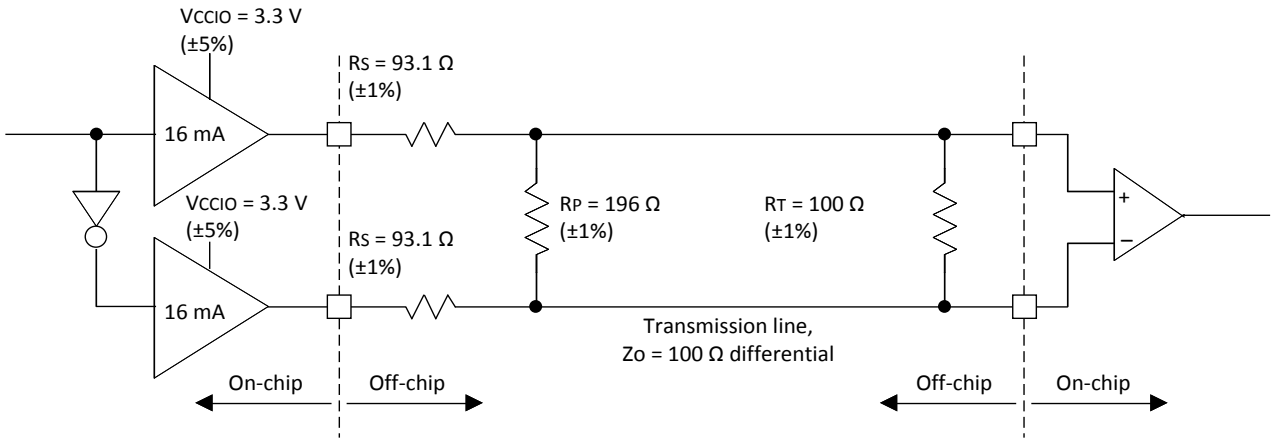


Figure 3.3. Differential LVPECL33

Over recommended operating conditions.

Table 3.16. LVPECL33 DC Conditions

Parameter	Description	Typical	Unit
V_{CCIO}	Output Driver Supply (±5%)	3.30	V
Z_{OUT}	Driver Impedance	10	Ω
R_S	Driver Series Resistor (±1%)	93	Ω
R_P	Driver Parallel Resistor (±1%)	196	Ω
R_T	Receiver Termination (±1%)	100	Ω
V_{OH}	Output High Voltage	2.05	V
V_{OL}	Output Low Voltage	1.25	V
V_{OD}	Output Differential Voltage	0.80	V
V_{CM}	Output Common Mode Voltage	1.65	V
Z_{BACK}	Back Impedance	100.5	Ω
I_{DC}	DC Output Current	12.11	mA

Note: For input buffer, see LVDS Table 3.13 on page 55.

3.18. External Switching Characteristics

Over recommended commercial operating conditions.

Table 3.22. ECP5/ECP5-5G External Switching Characteristics

Parameter	Description	Device	–8		–7		–6		Unit
			Min	Max	Min	Max	Min	Max	
Clocks									
Primary Clock									
f_{MAX_PRI}	Frequency for Primary Clock Tree	—	—	370	—	303	—	257	MHz
t_{W_PRI}	Clock Pulse Width for Primary Clock	—	0.8	—	0.9	—	1.0	—	ns
t_{SKEW_PRI}	Primary Clock Skew within a Device	—	—	420	—	462	—	505	ps
Edge Clock									
f_{MAX_EDGE}	Frequency for Edge Clock Tree	—	—	400	—	350	—	312	MHz
t_{W_EDGE}	Clock Pulse Width for Edge Clock	—	1.175	—	1.344	—	1.50	—	ns
t_{SKEW_EDGE}	Edge Clock Skew within a Bank	—	—	160	—	180	—	200	ps
Generic SDR Input									
General I/O Pin Parameters Using Dedicated Primary Clock Input without PLL									
t_{CO}	Clock to Output - PIO Output Register	All Devices	—	5.4	—	6.1	—	6.8	ns
t_{SU}	Clock to Data Setup - PIO Input Register	All Devices	0	—	0	—	0	—	ns
t_{H}	Clock to Data Hold - PIO Input Register	All Devices	2.7	—	3	—	3.3	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	All Devices	1.2	—	1.33	—	1.46	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Data Input Delay	All Devices	0	—	0	—	0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	All Devices	—	400	—	350	—	312	MHz
General I/O Pin Parameters Using Dedicated Primary Clock Input with PLL									
t_{COPLL}	Clock to Output - PIO Output Register	All Devices	—	3.5	—	3.8	—	4.1	ns
t_{SUPLL}	Clock to Data Setup - PIO Input Register	All Devices	0.7	—	0.78	—	0.85	—	ns
t_{HPLL}	Clock to Data Hold - PIO Input Register	All Devices	0.8	—	0.89	—	0.98	—	ns
t_{SU_DELPLL}	Clock to Data Setup - PIO Input Register with Data Input Delay	All Devices	1.6	—	1.78	—	1.95	—	ns

Table 3.22. ECP5/ECP5-5G External Switching Characteristics *(Continued)*

Parameter	Description	Device	–8		–7		–6		Unit
			Min	Max	Min	Max	Min	Max	
Generic DDR Output									
Generic DDRX1 Outputs With Clock and Data Centered at Pin (GDDRX1_TX.SCLK.Centered) Using PCLK Clock Input - Figure 3.6									
$t_{DVB\_GDDRX1\_centered}$	Data Output Valid before CLK Output	All Devices	–0.67	—	–0.67	—	–0.67	—	ns + 1/2 UI
$t_{DVA\_GDDRX1\_centered}$	Data Output Valid after CLK Output	All Devices	–0.67	—	–0.67	—	–0.67	—	ns + 1/2 UI
$f_{DATA\_GDDRX1\_centered}$	GDDRX1 Data Rate	All Devices	—	500	—	500	—	500	Mb/s
$f_{MAX\_GDDRX1\_centered}$	GDDRX1 CLK Frequency (SCLK)	All Devices	—	250	—	250	—	250	MHz
Generic DDRX1 Outputs With Clock and Data Aligned at Pin (GDDRX1_TX.SCLK.Aligned) Using PCLK Clock Input - Figure 3.9									
$t_{DIB\_GDDRX1\_aligned}$	Data Output Invalid before CLK Output	All Devices	–0.3	—	–0.3	—	–0.3	—	ns
$t_{DIA\_GDDRX1\_aligned}$	Data Output Invalid after CLK Output	All Devices	—	0.3	—	0.3	—	0.3	ns
$f_{DATA\_GDDRX1\_aligned}$	GDDRX1 Data Rate	All Devices	—	500	—	500	—	500	Mb/s
$f_{MAX\_GDDRX1\_aligned}$	GDDRX1 CLK Frequency (SCLK)	All Devices	—	250	—	250	—	250	MHz
Generic DDRX2 Outputs With Clock and Data Centered at Pin (GDDRX2_TX.ECLK.Centered) Using PCLK Clock Input, Left and Right sides Only - Figure 3.8									
$t_{DVB\_GDDRX2\_centered}$	Data Output Valid Before CLK Output	All Devices	–0.442	—	–0.56	—	–0.676	—	ns + 1/2 UI
$t_{DVA\_GDDRX2\_centered}$	Data Output Valid After CLK Output	All Devices	—	0.442	—	0.56	—	0.676	ns + 1/2 UI
$f_{DATA\_GDDRX2\_centered}$	GDDRX2 Data Rate	All Devices	—	800	—	700	—	624	Mb/s
$f_{MAX\_GDDRX2\_centered}$	GDDRX2 CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz
Generic DDRX2 Outputs With Clock and Data Aligned at Pin (GDDRX2_TX.ECLK.Aligned) Using PCLK Clock Input, Left and Right sides Only - Figure 3.9									
$t_{DIB\_GDDRX2\_aligned}$	Data Output Invalid before CLK Output	All Devices	–0.16	—	–0.18	—	–0.2	—	ns
$t_{DIA\_GDDRX2\_aligned}$	Data Output Invalid after CLK Output	All Devices	—	0.16	—	0.18	—	0.2	ns
$f_{DATA\_GDDRX2\_aligned}$	GDDRX2 Data Rate	All Devices	—	800	—	700	—	624	Mb/s
$f_{MAX\_GDDRX2\_aligned}$	GDDRX2 CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz
Video DDRX71 Outputs With Clock and Data Aligned at Pin (GDDRX71_TX.ECLK) Using PLL Clock Input, Left and Right sides Only - Figure 3.12									
$t_{DIB\_LVDS71\_i}$	Data Output Invalid before CLK Output	All Devices	–0.16	—	–0.18	—	–0.2	—	ns + (i) * UI
$t_{DIA\_LVDS71\_i}$	Data Output Invalid after CLK Output	All Devices	—	0.16	—	0.18	—	0.2	ns + (i) * UI
f_{DATA_LVDS71}	DDR71 Data Rate	All Devices	—	756	—	620	—	525	Mb/s
f_{MAX_LVDS71}	DDR71 CLK Frequency (ECLK)	All Devices	—	378	—	310	—	262.5	MHz
Memory Interface									
DDR2/DDR3/DDR3L/LPDDR2/LPDDR3 READ (DQ Input Data are Aligned to DQS)									
t_{DVBDQ_DDR2} t_{DVBDQ_DDR3} t_{DVBDQ_DDR3L} t_{DVBDQ_LPDDR2} t_{DVBDQ_LPDDR3}	Data Output Valid before DQS Input	All Devices	—	–0.26	—	–0.317	—	–0.374	ns + 1/2 UI
t_{DVADQ_DDR2} t_{DVADQ_DDR3} t_{DVADQ_DDR3L} t_{DVADQ_LPDDR2} t_{DVADQ_LPDDR3}	Data Output Valid after DQS Input	All Devices	0.26	—	0.317	—	0.374	—	ns + 1/2 UI

Table 3.22. ECP5/ECP5-5G External Switching Characteristics *(Continued)*

Revision History

Date	Version	Section	Change Summary
March 2018	1.9	All	Updated formatting and page referencing.
		General Description	Updated Table 1.1. ECP5 and ECP5-5G Family Selection Guide. Added caBGA256 package in LFE5U-45.
		Architecture	Added a row for SGMII in Table 2.13. LFE5UM/LFE5UM5G SERDES Standard Support. Updated footnote #1.
		DC and Switching Characteristics	Updated Table 3.2. Recommended Operating Conditions.
			Added 2 rows and updated values in Table 3.7. DC Electrical Characteristics.
			Updated Table 3.8. ECP5/ECP5-5G Supply Current (Standby).
			Updated Table 3.11. sysI/O Recommended Operating Conditions.
			Updated Table 3.12. Single-Ended DC Characteristics.
			Updated Table 3.13. LVDS.
			Updated Table 3.14. LVDS25E DC Conditions.
			Updated Table 3.21. ECP5/ECP5-5G Maximum I/O Buffer Speed.
			Updated Table 3.28. Receiver Total Jitter Tolerance Specification.
			Updated header name of section 3.28 CPRI LV E.24/SGMII(2.5Gbps) Electrical and Timing Characteristics.
			Updated header name of section 3.29 Gigabit Ethernet/SGMII(1.25Gbps)/CPRI LV E.12 Electrical and Timing Characteristics
		Pinout Information	Updated table in section 4.3.2 LFE5U.
		Ordering Information	Added table rows in 5.2.1 Commercial.
			Added table rows in 5.2.2 Industrial.
		Supplemental Information	Updated For Further Information section.
November 2017	1.8	General Description	Updated Table 1.1. ECP5 and ECP5-5G Family Selection Guide. Added caBGA256 package in LFE5U-12 and LFE5U-25.

(Continued)

Date	Version	Section	Change Summary
April 2017	1.7	All	Changed document number from DS1044 to FPGA-DS-02012.
		General Description	Updated Features section. Changed “1.1 V core power supply” to “1.1 V core power supply for ECP5, 1.2 V core power supply for ECP5UM5G”.
		Architecture	Updated Overview section. Change “The ECP5/ECP5-5G devices use 1.1 V as their core voltage” to “The ECP5 devices use 1.1V, ECP5UM5G devices use 1.2V as their core voltage”
		DC and Switching Characteristics	Updated Table 3.2. Recommended Operating Conditions Added ECP5-5G on VCC to be 1.2V +/- 5% Added ECP5-5G on VCCA to be 1.2V +/- 3% Updated Table 3.8. ECP5/ECP5-5G Supply Current (Standby) Changed “Core Power Supply Current” for ICC on LFE5UM5G devices Changed “SERDES Power Supply Current (Per Dual)” for ICCA on LFE5UM5G devices Updated Table 3.20. Register-to-Register Performance. Remove “(DDR/SDR)” from DSP Function Changed DSP functions to 225 MHz
		Pinout Information	Update Section 4.1 Signal Description. Revised Vcc Description to “Power supply pins for core logic. Dedicated pins. VCC = 1.1 V (ECP5), 1.2 V (ECP5UM5G)”
February 2016	1.6	All	Changed document status from Preliminary to Final.
		General Description	Updated Features section. Changed “24K to 84K LUTs” to “12K to 84K LUTs”. Added LFE5U-12 column to Table 1.1. ECP5 and ECP5-5G Family Selection Guide.
		DC and Switching Characteristics	Updated Power up Sequence section. Identified typical ICC current for specific devices in Table 3.8. ECP5/ECP5-5G Supply Current (Standby). Updated values in Table 3.9. ECP5. Updated values in Table 3.10. ECP5-5G. Added values to –8 Timing column of Table 3.19. Pin-to-Pin Performance. Added values to –8 Timing column of Table 3.20. Register-to-Register Performance. Changed LFE5-45 to All Devices in Table 3.22. ECP5/ECP5-5G External Switching Characteristics. Added table notes to Table 3.31. PCIe (5 Gb/s). Added table note to Table 3.32. CPRI LV2 E.48 Electrical and Timing Characteristics.
		Pinout Information	Added LFE5U-12 column to the table in LFE5U section.
		Ordering Information	Updated LFE5U in ECP5/ECP5-5G Part Number Description section: added 12 F = 12K LUTs to Logic Capacity. Added LFE5U-12F information to Ordering Part Numbers section.

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